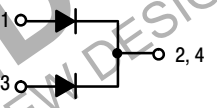
MBR2030CTLG

Switch-mode Dual Schottky Power Rectifier

ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 30 VOLTS



Features and Benefits

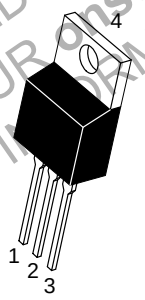
- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop (0.4 Max @ 10 A, T_C = 150°C)
- High Junction Temperature
- High dv/dt Capability
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This Device is Pb−Free and is RoHS Compliant*

Applications

- Power Supply − Output Rectification
- Power Management − ORING
- Instrumentation

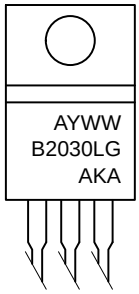
Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Sec
- ESD Rating: Human Body Model 3B
  Machine Model C



TO−220
CASE 221A
STYLE 6

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
B2030L	= Device Code
G	= Pb−Free Package
AKA	= Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR2030CTLG	TO−220 (Pb−Free)	50 Units/Rail

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Forward Current (T_C = 167°C) Per Diode Per Device	$I_{F(AV)}$	 10 20	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, T_C = 166°C)	I_{FRM}	10	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	A
Operating Junction Temperature (Note 1)	T_J	−65 to +175	°C
Storage Temperature	T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction−to−Case (Min. Pad)	$R_{\theta JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction−to−Ambient (Min. Pad)	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) (i_F = 10 Amps, T_J= 25°C) (i_F = 10 Amps, T_J = 150°C) (i_F = 20 Amps, T_J = 25°C) (i_F = 20 Amps, T_J = 150°C)	v_F	 − − − −	 0.45 0.32 0.51 0.41	 0.52 0.40 0.58 0.48	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_J = 25°C) (Rated dc Voltage, T_J = 100°C) (Rated dc Voltage, T_J = 125°C)	i_R	 − − −	 0.11 10 −	 5.0 40 75	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

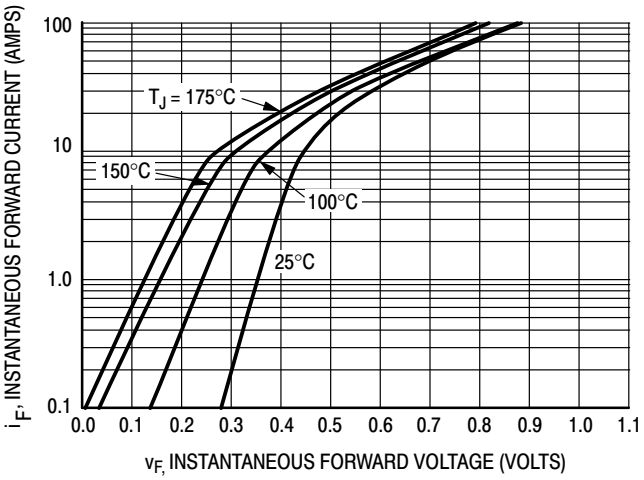


Figure 1. Typical Forward Voltage

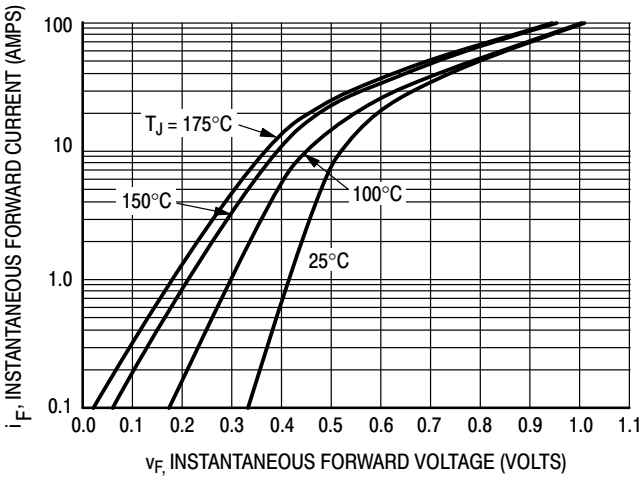


Figure 2. Maximum Forward Voltage

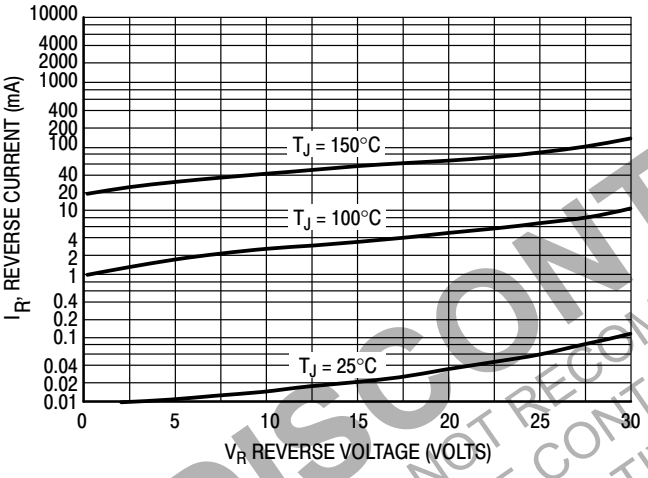


Figure 3. Typical Reverse Current

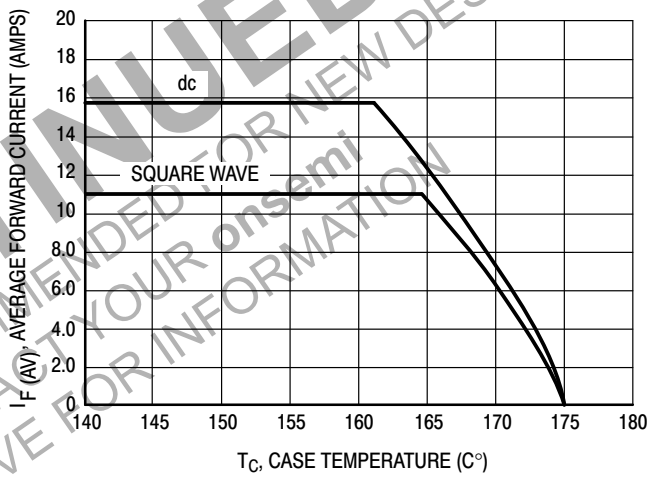


Figure 4. Current Derating, Case Per Leg

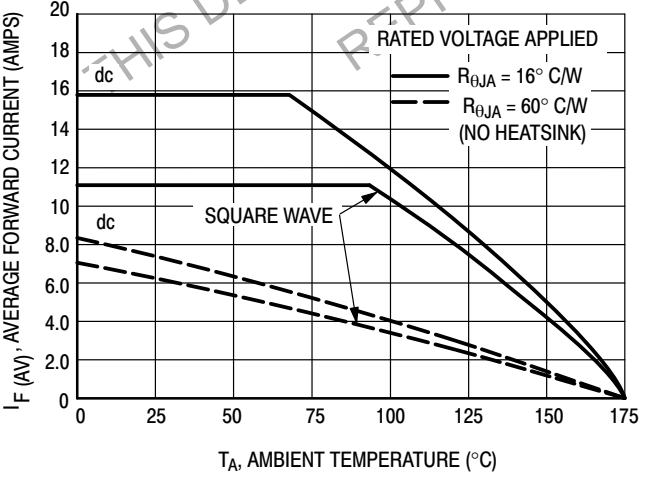


Figure 5. Current Derating, Ambient Per Leg

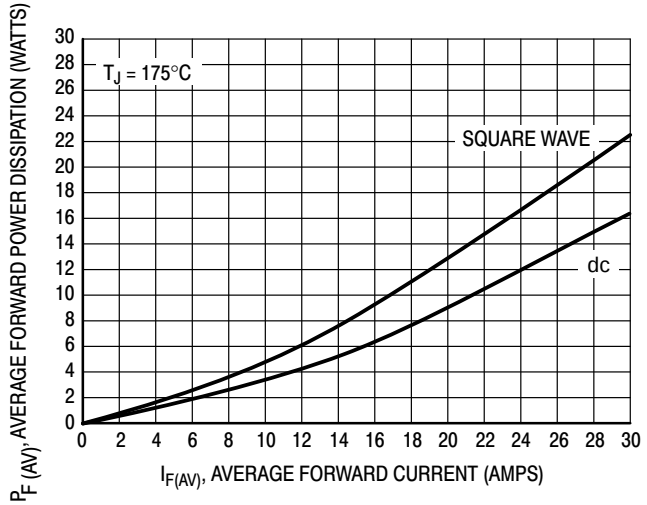


Figure 6. Forward Power Dissipation

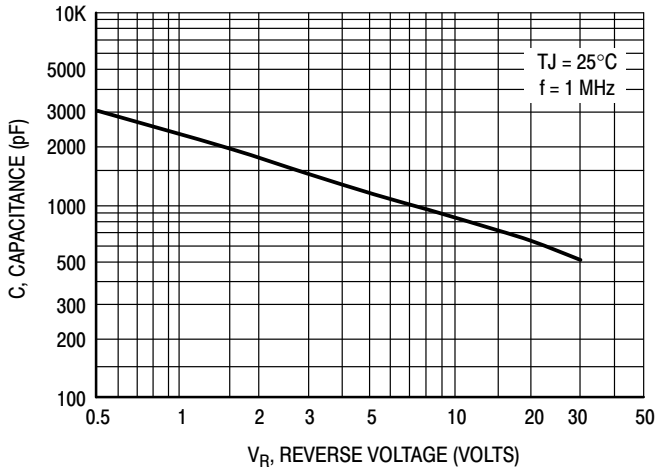
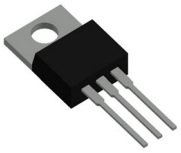
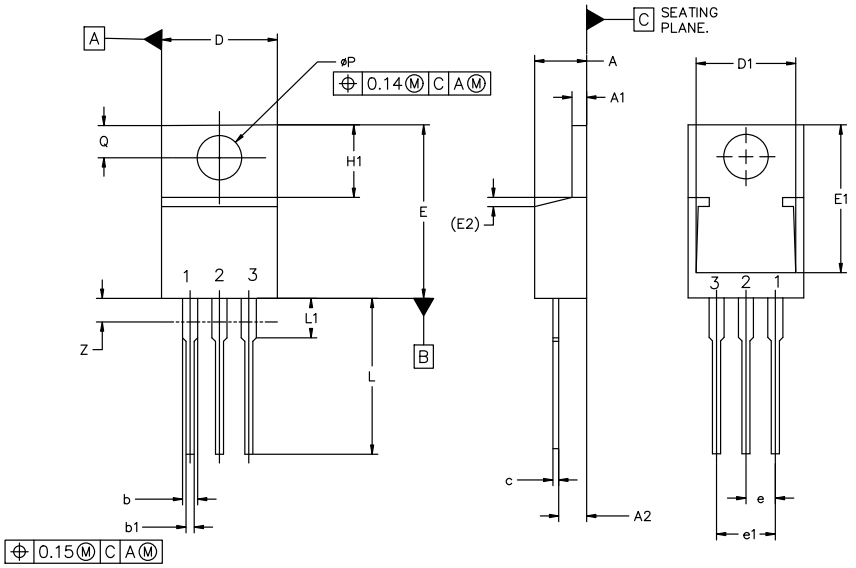


Figure 7. Typical Capacitance



TO−220−3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	−.−−	−.−−	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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DESCRIPTION:	**TO−220−3 10.10x15.12x4.45, 2.54P**	**PAGE 1 OF 1**

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